

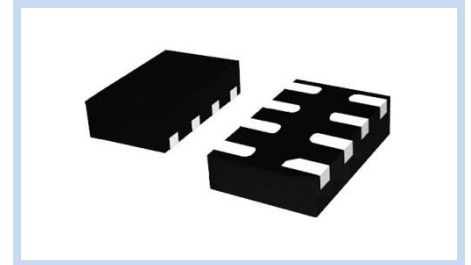
ESD Suppressor 3V 2-Bidirectional DFN2010

ME32B15D2010

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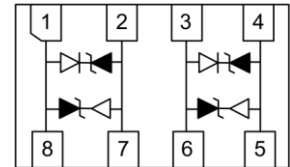
FEATURE

- IEC 61000-4-2 ESD: $\pm 20\text{KV}$ (Air) $\pm 20\text{KV}$ (Contact)
- ESD Protection for two Bidirectional Channels
- Low Leakage Current
- Low Clamping Voltage
- Solid-State Silicon-Avalanche Technology



APPLICATION

- 10/100/1000 Ethernet
- LAN/WAN Device
- Switching Systems
- Computers
- Instruments



MAXIMUM RATINGS AND CHARACTERISTICS

Parameter	Symbol	Value	Unit
ESD Voltage (Contact discharge)	V_{ESD}	± 20	KV
ESD Voltage (Air discharge)		± 20	
Peak Pulse Current ($t_p=8/20\mu s$)	I_{PP}	3	A
Operating & Storage Temperature Range	T_J, T_{STG}	$-55\sim+150$	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

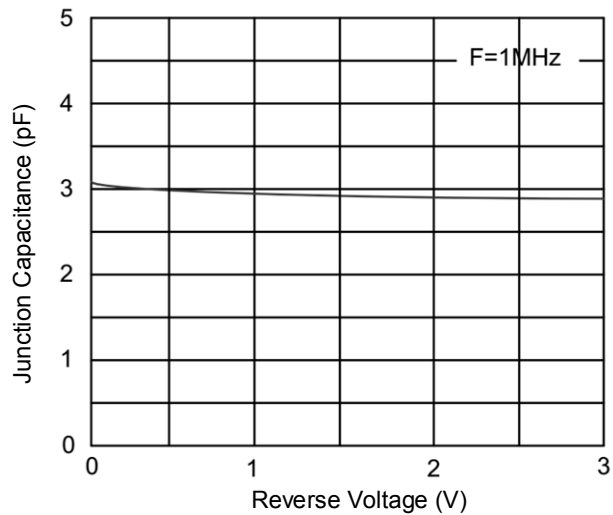
Parameter	Condition	Symbol	Min.	Typ.	Max.	Unit
Reverse Stand-Off Voltage	--	V_{RWM}	--	--	3	V
Reverse Breakdown Voltage	$I_{BR}=1\text{mA}$	V_{BR}	3.5	--	--	V
Reverse Leakage Current	$V_R=3\text{V}$	I_R	--	--	1	μA
Clamping Voltage	$I_{PP}=3\text{A}, t_p=8/20\mu s$	V_C	--	15	--	V
Off State Junction Capacitance	$V_{dc}=0, f=1\text{MHz}$	C_J	--	3	--	pF

Notes:

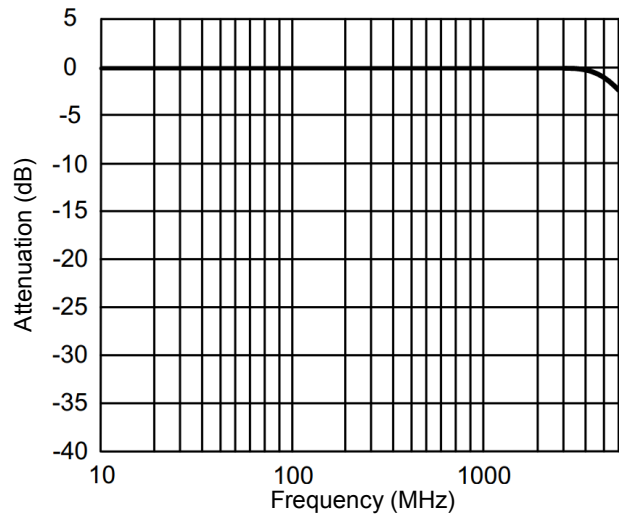
1. $T_J=25^{\circ}\text{C}$ unless otherwise specified

CHARACTERISTIC CURVES

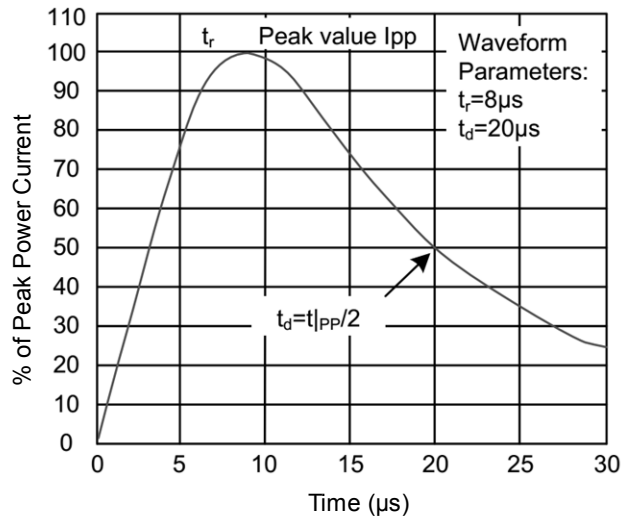
Capacitance vs. Bias Voltage



Insertion Loss (S21) I/O to GND



Pulse Waveform



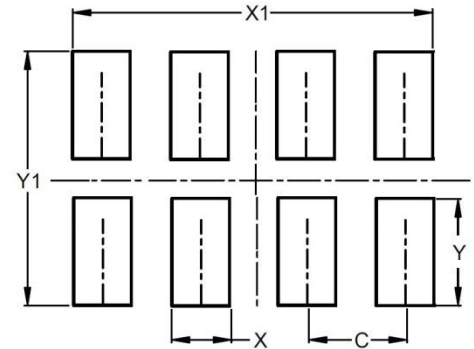
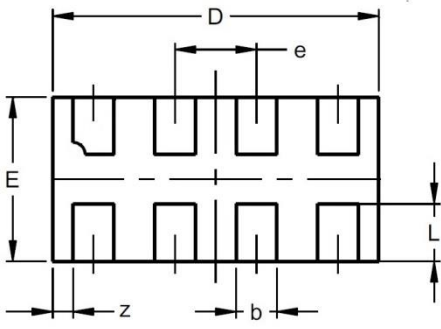
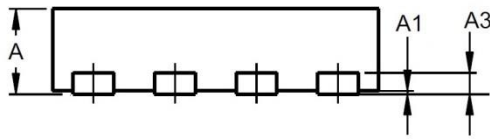
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DIMENSIONS AND RECOMMENDED LAND PATTERN

Item	Min (mm)	Max (mm)
A	0.45	0.55
A1	0.00	0.04
A3	0.11	0.11
b	0.20	0.30
D	1.92	2.07
E	0.92	1.07
e	0.50	0.50
L	0.27	0.42
C	0.50	0.50
X	0.30	0.30
X1	1.80	1.80
Y	0.60	0.60
Y1	1.40	1.40



*Specifications subject to change without notice.